



#9/B  
Hedg  
8/1/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Hideo YAMANAKA et al.

Art Unit: 1762

Serial No. 09/646,680

Examiner: E. Fuller

Filed: September 20, 2000

For: FILM FORMING METHOD AND FILM FORMING APPARATUS

REQUEST FOR RECONSIDERATION

Commissioner for Patents  
Washington, D.C. 20231

RECEIVED  
JUL 31 2002  
TECHNOLOGY CENTER 1700

Sir:

In response to the non-final Office Action mailed on March 27, 2002, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please replace the paragraph beginning at page 20, line 2 with the following rewritten paragraph.

-- To carry out the DC-bias catalyzed CVD method, the degree of vacuum in the deposition chamber 44 is set at  $10^{-6}$  to  $10^{-8}$  Torr, and the hydrogen-based carrier gas is supplied at 100 to 200 SCCM (standard cc per minute). After the catalyzer is heated to a predetermined temperature for activation, the reaction gas 40 made of the silicon hydride (e.g., mono-silane) gas at 1 to 20 SCCM (including an appropriate quantity of the doping gas made of